

N-channel TrenchMOS logic level FET 12 June 2014

Product data sheet

#### 1. General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

### 2. Features and benefits

- Low conduction losses due to low on-state resistance
- Q101 compliant
- Suitable for logic level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

### 3. Applications

- 12 V and 24 V loads
- Automotive and general purpose power switching
- Motors, lamps and solenoids

#### 4. Quick reference data

Table 1. C	Quick reference data						
Symbol	Parameter	Conditions	N	lin	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-		-	55	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 5 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u> ; <u>Fig. 3</u>	-		-	11	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>	-		-	36	W
Static chara	acteristics						
R <sub>DSon</sub>	drain-source on-state	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 5 A; T <sub>j</sub> = 25 °C	-		97	125	mΩ
	resistance	V <sub>GS</sub> = 5 V; I <sub>D</sub> = 5 A; T <sub>j</sub> = 175 °C; Fig. 11; Fig. 12	-		-	280	mΩ
		$V_{GS}$ = 4.5 V; I <sub>D</sub> = 5 A; T <sub>j</sub> = 25 °C	-		-	155	mΩ
		V <sub>GS</sub> = 5 V; I <sub>D</sub> = 5 A; T <sub>j</sub> = 25 °C; <u>Fig. 11</u> ; <u>Fig. 12</u>	-		120	140	mΩ
Dynamic ch	naracteristics	· · · · · · · · · · · · · · · · · · ·	1				
Q <sub>GD</sub>	gate-drain charge	$V_{GS}$ = 5 V; I <sub>D</sub> = 5 A; V <sub>DS</sub> = 44 V; T <sub>j</sub> = 25 °C; <u>Fig. 13</u>	-		2.6	-	nC

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Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
Avalanche ruggedness							
E <sub>DS(AL)S</sub>	non-repetitive drain- source avalanche energy	$I_D$ = 11 A; $V_{sup} \le 55$ V; $R_{GS}$ = 50 Ω; $V_{GS}$ = 5 V; $T_{j(init)}$ = 25 °C; unclamped		-	-	16	mJ

### 5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	D
2	D	Drain		
3	S	source		G
mb	D	mounting base; connected to drain	DPAK (SOT428)	mbb076 S

### 6. Ordering information

Table 3.   Ordering information							
Type number	Package						
	Name	Description	Version				
BUK92150-55A	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428				
BUK92150-55A/CD	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428				

### 7. Marking

Table 4. Marking codes	
Type number	Marking code
BUK92150-55A	9215055A
BUK92150-55A/CD	

### 8. Limiting values

#### Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	55	V

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Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DGR</sub>	drain-gate voltage	R <sub>GS</sub> 20 kΩ	-	55	V
V <sub>GS</sub>	gate-source voltage		-15	15	V
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>	-	36	W
I <sub>D</sub>	drain current	T <sub>mb</sub> = 25 °C; V <sub>GS</sub> = 5 V; <u>Fig. 2; Fig. 3</u>	-	11	А
		T <sub>mb</sub> = 100 °C; V <sub>GS</sub> = 5 V; <u>Fig. 3</u>	-	7.8	А
I <sub>DM</sub>	peak drain current	$T_{mb}$ = 25 °C; pulsed; $t_p \le 10 \ \mu$ s; Fig. 2	-	44	А
T <sub>stg</sub>	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
Source-drai	in diode				
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	-	11	А
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^\circ C$	-	44	А
Avalanche r	ruggedness	, ,			
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D$ = 11 A; $V_{sup} \le 55$ V; $R_{GS}$ = 50 Ω; $V_{GS}$ = 5 V; $T_{j(init)}$ = 25 °C; unclamped	-	16	mJ

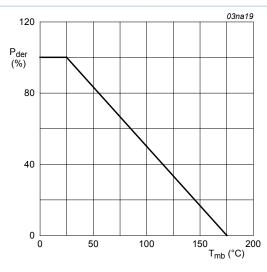
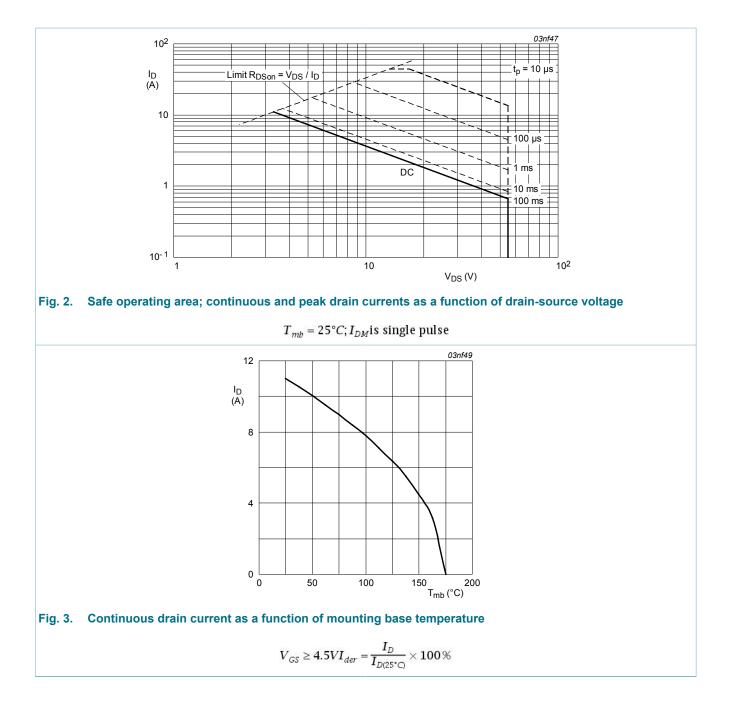


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

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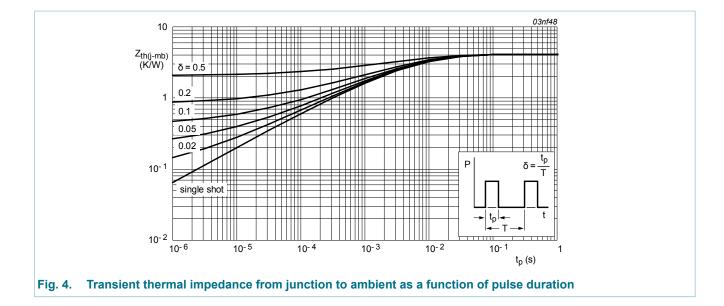


#### **Thermal characteristics** 9.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	<u>Fig. 4</u>	-	-	4.1	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient		-	71.4	-	K/W

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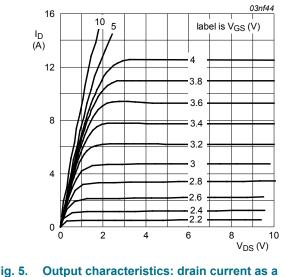


### **10. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics	1				
V <sub>(BR)DSS</sub> drain-source breakdown voltage		$I_D$ = 0.25 mA; $V_{GS}$ = 0 V; $T_j$ = 25 °C	55	-	-	V
	breakdown voltage	$I_D$ = 0.25 mA; $V_{GS}$ = 0 V; $T_j$ = -55 °C	50	-	-	V
V <sub>GS(th)</sub> gate-source thresh voltage	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 10	-	-	2.3	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ Fig. 10	1	1.5	2	V
		I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 175 °C; Fig. 10	0.5	-	-	V
I <sub>DSS</sub> drain leakage current	drain leakage current	V <sub>DS</sub> = 55 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 175 °C	-	-	500	μA
		$V_{DS}$ = 55 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-	0.05	10	μA
I <sub>GSS</sub> gate leakage current	gate leakage current	$V_{GS}$ = 10 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	2	100	nA
		$V_{GS}$ = -10 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	2	100	nA
R <sub>DSon</sub>	drain-source on-state	$V_{GS}$ = 10 V; I <sub>D</sub> = 5 A; T <sub>j</sub> = 25 °C	-	97	125	mΩ
	resistance	V <sub>GS</sub> = 5 V; I <sub>D</sub> = 5 A; T <sub>j</sub> = 175 °C; Fig. 11; Fig. 12	-	-	280	mΩ
		$V_{GS}$ = 4.5 V; I <sub>D</sub> = 5 A; T <sub>j</sub> = 25 °C	-	-	155	mΩ
		V <sub>GS</sub> = 5 V; I <sub>D</sub> = 5 A; T <sub>j</sub> = 25 °C; <u>Fig. 11;</u> Fig. 12	-	120	140	mΩ

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Dynamic cl	haracteristics					
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 5 A; V <sub>DS</sub> = 44 V; V <sub>GS</sub> = 5 V; T <sub>j</sub> = 25 °C; <u>Fig. 13</u>	-	6	-	nC
Q <sub>GS</sub>	gate-source charge		-	0.76	-	nC
Q <sub>GD</sub>	gate-drain charge		-	2.6	-	nC
C <sub>iss</sub>	input capacitance	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 25 V; f = 1 MHz; T <sub>j</sub> = 25 °C; <u>Fig. 14</u>	-	240	338	pF
C <sub>oss</sub>	output capacitance		-	50	65	pF
C <sub>rss</sub>	reverse transfer capacitance		-	40	58	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 20 V; R <sub>L</sub> = 3.3 Ω; V <sub>GS</sub> = 5 V; R <sub>G(ext)</sub> = 10 Ω; T <sub>j</sub> = 25 °C	-	8	-	ns
t <sub>r</sub>	rise time		-	57	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	16	-	ns
t <sub>f</sub>	fall time	_	-	13	-	ns
L <sub>D</sub>	internal drain inductance	measured from drain to centre of die; T <sub>j</sub> = 25 °C	-	2.5	-	nH
L <sub>S</sub>	internal source inductance	measured from source lead to source bond pad; $T_j = 25 \ ^{\circ}C$	-	7.5	-	nH
Source-dra	in diode					
V <sub>SD</sub>	source-drain voltage	$I_{S}$ = 15 A; $V_{GS}$ = 0 V; $T_{j}$ = 25 °C; <u>Fig. 15</u>	-	0.85	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_{S}$ = 20 A; d $I_{S}$ /dt = -100 A/µs;	-	24	-	ns
Q <sub>r</sub>	recovered charge	$V_{GS}$ = -10 V; $V_{DS}$ = 30 V; $T_j$ = 25 °C		26	-	nC







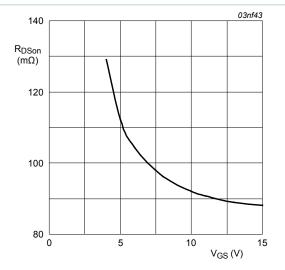


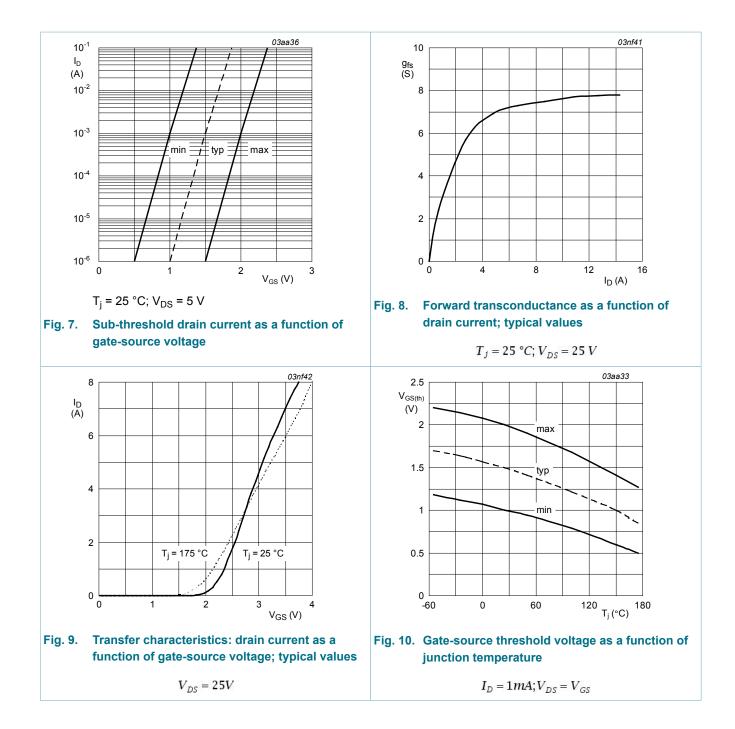
Fig. 6. Drain-source on-state resistance as a function of gate-source voltage; typical values

 $T_j = 25^{\circ}C; I_D = 5A$ 

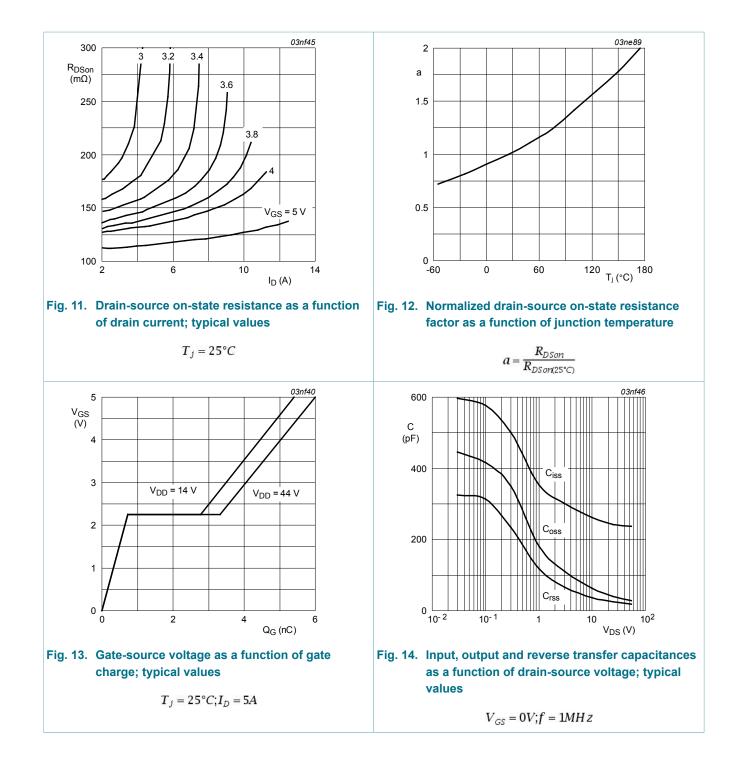
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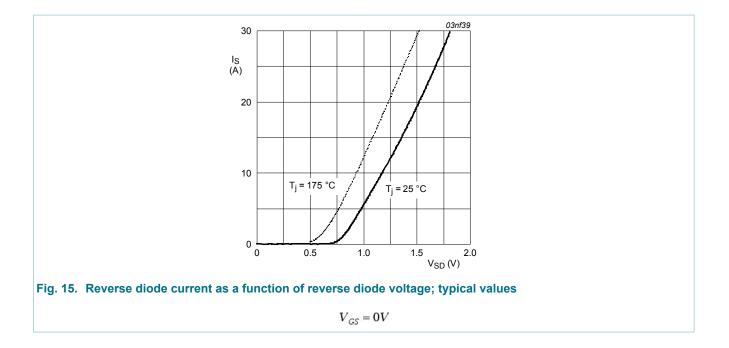
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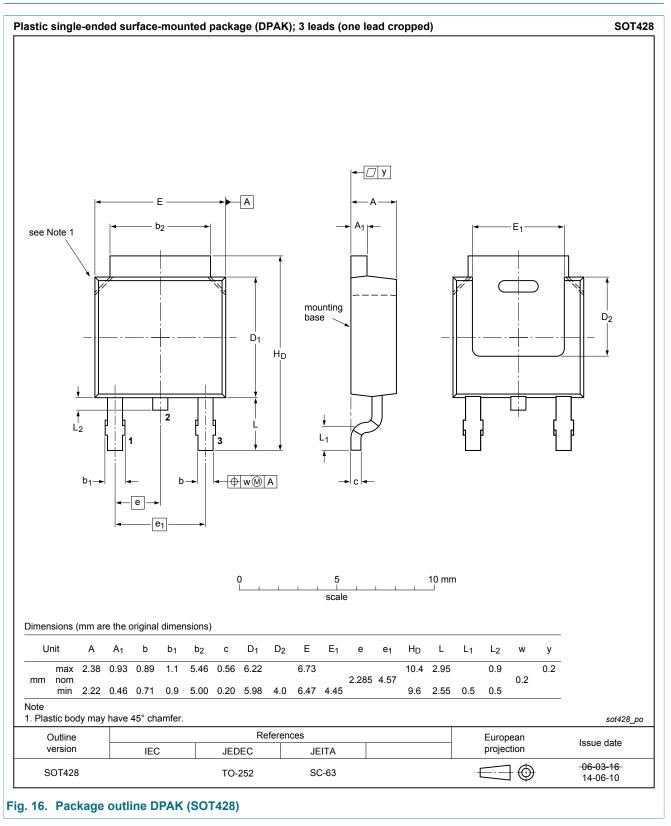
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#### 11. Package outline



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#### 12. Legal information

#### 12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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[2] The term 'short data sheet' is explained in section "Definitions".

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